March 2014

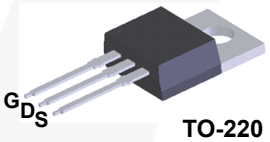
FCP11N60/FCPF11N60

General Description

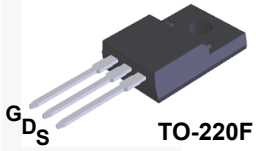
SuperFET® MOSFET is Fairchild Semiconductor's first genera-tion of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switch-ing performance, dv/dt rate and higher avalanche energy. Con-sequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.

Features

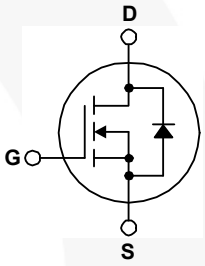
- 650V @T_j = 150°C
- Typ. Rds(on)=0.32Ω
- Ultra low gate charge (typ. Qg=40nC)
- Low effective output capacitance (typ. Coss.eff=95pF)
- 100% avalanche tested
- RoHS Compliant



TO-220



TO-220F



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FCP11N60	FCPF11N60	Units
I_D	Drain Current - Continuous (T_C = 25°C)		11	11*	A
	- Continuous (T_C = 100°C)		7	7*	A
I_{DM}	Drain Current - Pulsed	(Note 1)	33	33*	A
V_{GSS}	Gate-Source Voltage		± 30		V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	340		mJ
I_{AR}	Avalanche Current	(Note 1)	11		A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	12.5		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5		V/ns
P_D	Power Dissipation (T_C = 25°C)		125	36	W
	- Derate above 25°C		1.0	0.29	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300		°C

* Drain current limited by maximum junction termperature

Thermal Characteristics

Symbol	Parameter	FCP11N60	FCPF11N60	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.0	3.5	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP11N60	FCP11N60	TO-220	Tube	N/A	N/A	50 units
FCPF11N60	FCPF11N60	TO-220F	Tube	N/A	N/A	50 units
FCPF11N60T	FCPF11N60T	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA, T_J = 25°C	600	--	--	V
		V_{GS} = 0 V, I_D = 250 μA, T_J = 150°C	--	650	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.6	--	V/°C
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	V_{GS} = 0 V, I_D = 11 A	--	700	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 480 V, T_C = 125°C	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 5.5 A	--	0.32	0.38	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 5.5 A (Note 4)	--	9.7	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1148	1490	pF
C_{oss}	Output Capacitance		--	671	870	pF
C_{rss}	Reverse Transfer Capacitance		--	63	82	pF
C_{oss}	Output Capacitance	V_{DS} = 480 V, V_{GS} = 0 V, f = 1.0 MHz	--	35	--	pF
C_{oss} eff.	Effective Output Capacitance	V_{DS} = 0V to 480 V, V_{GS} = 0 V	--	95	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 300 V, I_D = 11 A, R_G = 25 Ω (Note 4, 5)	--	34	80	ns
t_r	Turn-On Rise Time		--	98	205	ns
$t_{d(off)}$	Turn-Off Delay Time		--	119	250	ns
t_f	Turn-Off Fall Time		--	56	120	ns
Q_g	Total Gate Charge	V_{DS} = 480 V, I_D = 11 A, V_{GS} = 10 V (Note 4, 5)	--	40	52	nC
Q_{gs}	Gate-Source Charge		--	7.2	--	nC
Q_{gd}	Gate-Drain Charge		--	21	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	11	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	33	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 11 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 11 A, dI_F / dt = 100 A/μs (Note 4)	--	390	--	ns
Q_{rr}	Reverse Recovery Charge		--	5.7	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I_{AS} = 5.5A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 11A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Characteristics

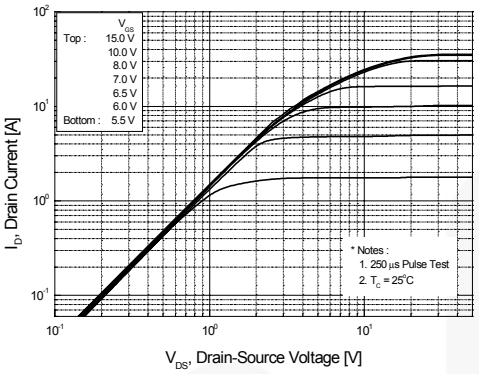


Figure 1. On-Region Characteristics

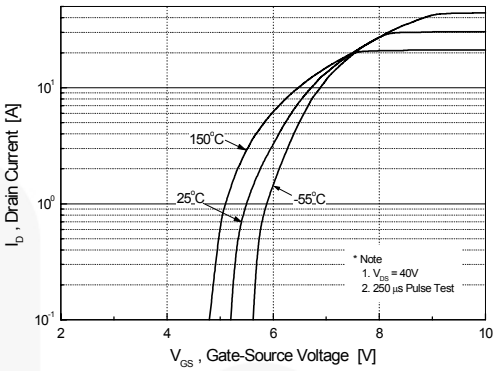


Figure 2. Transfer Characteristics

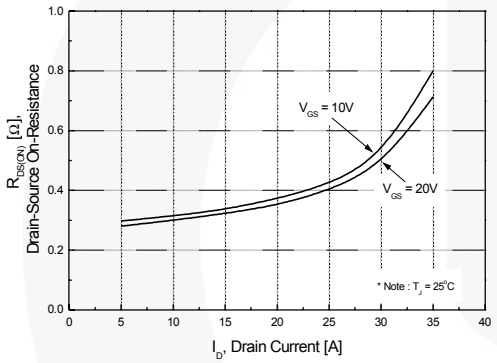


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

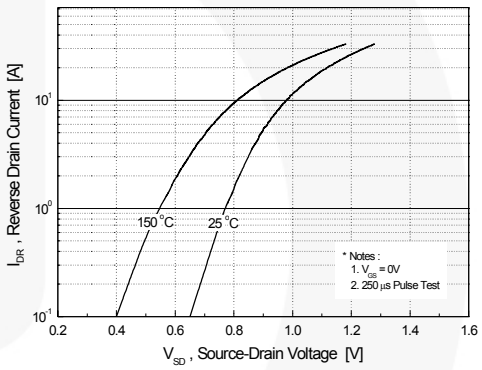


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

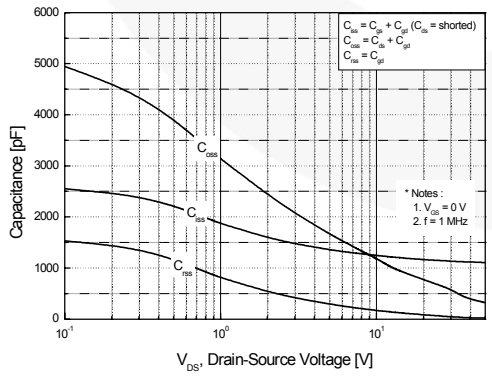


Figure 5. Capacitance Characteristics

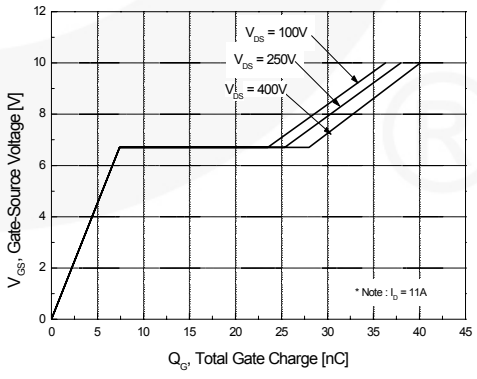


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

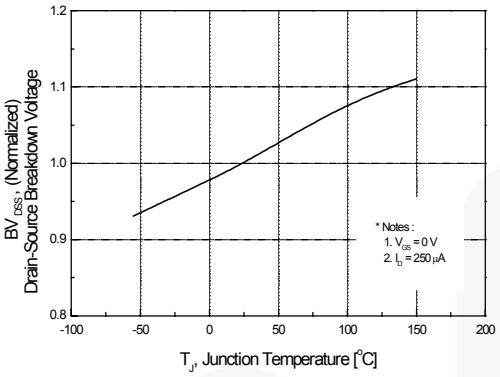


Figure 7. Breakdown Voltage Variation vs. Temperature

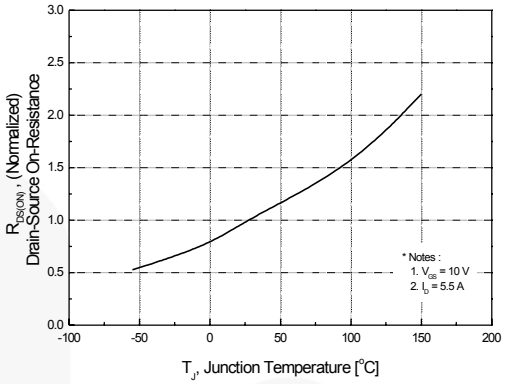


Figure 8. On-Resistance Variation vs. Temperature

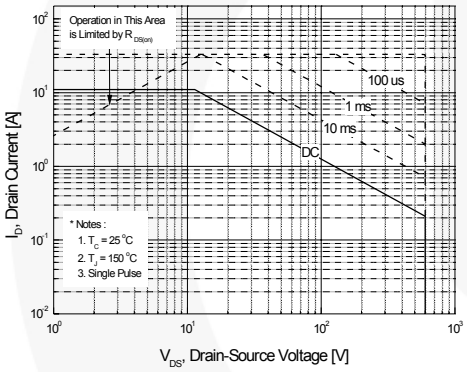


Figure 9-1. Maximum Safe Operating Area for FCP11N60

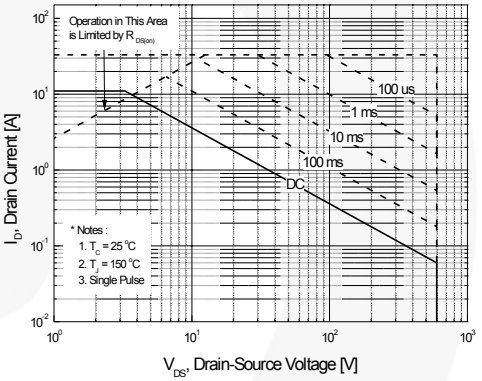


Figure 9-2. Maximum Safe Operating Area for FCPF11N60

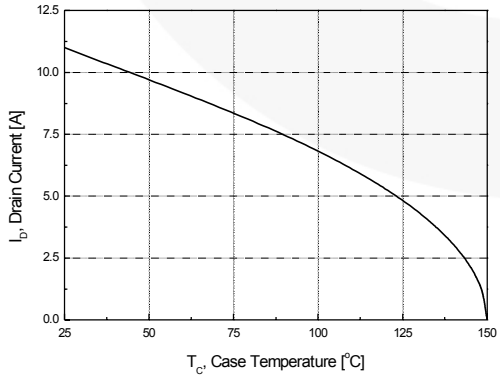


Figure 10. Maximum Drain Current vs. Case Temperature

Typical Characteristics (Continued)

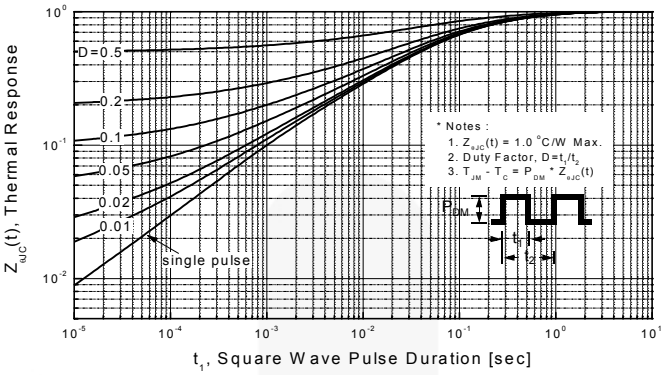


Figure 11-1. Transient Thermal Response Curve for FCP11N60

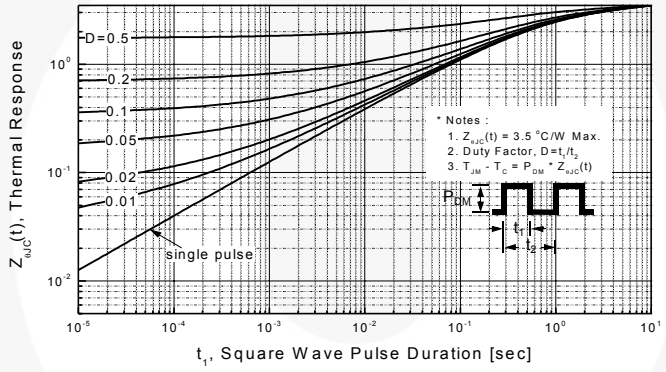


Figure 11-2. Transient Thermal Response Curve for FCPF11N60

Figure 12. Gate Charge Test Circuit & Waveform

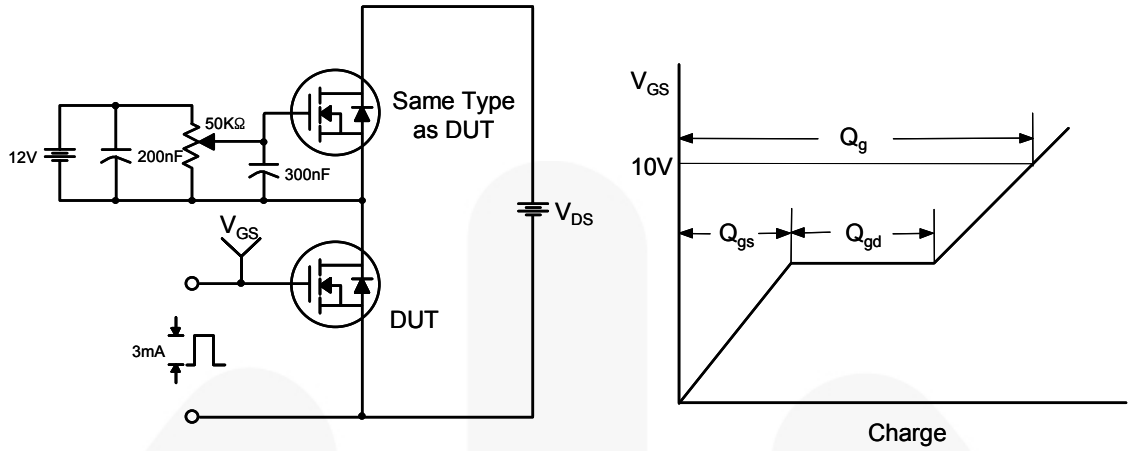


Figure 13. Resistive Switching Test Circuit & Waveforms

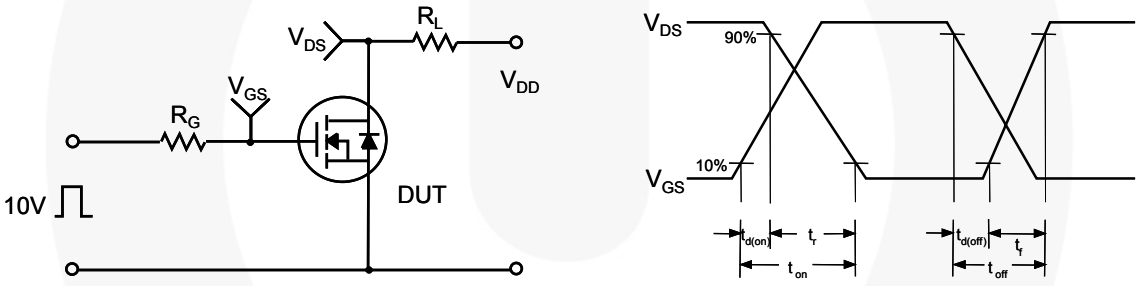


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

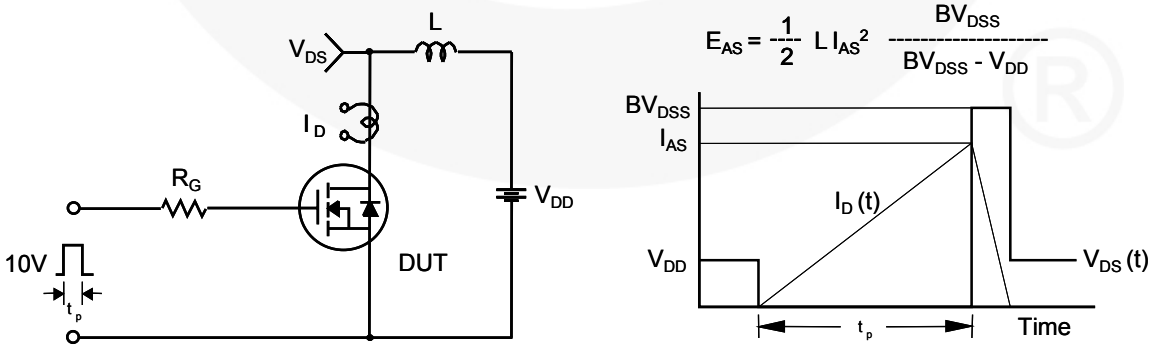
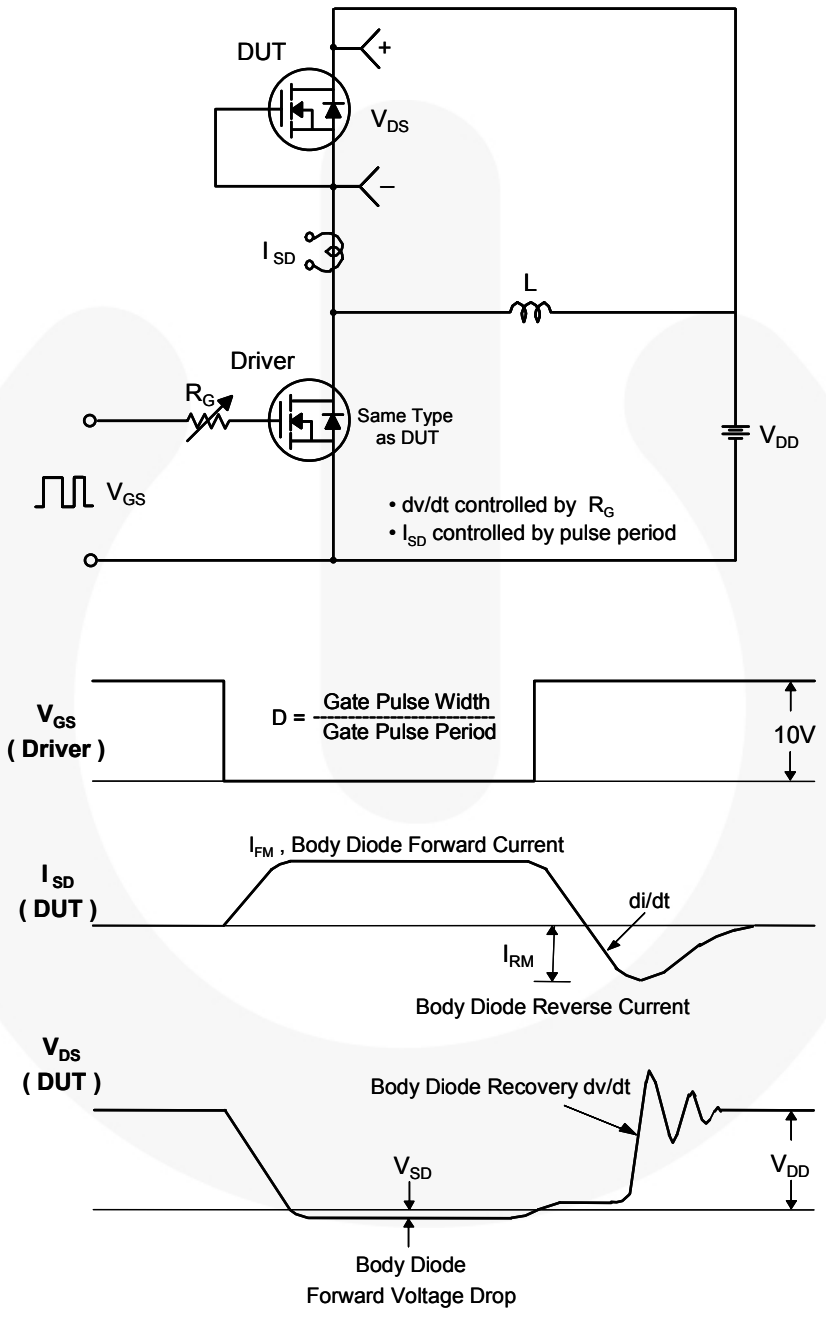
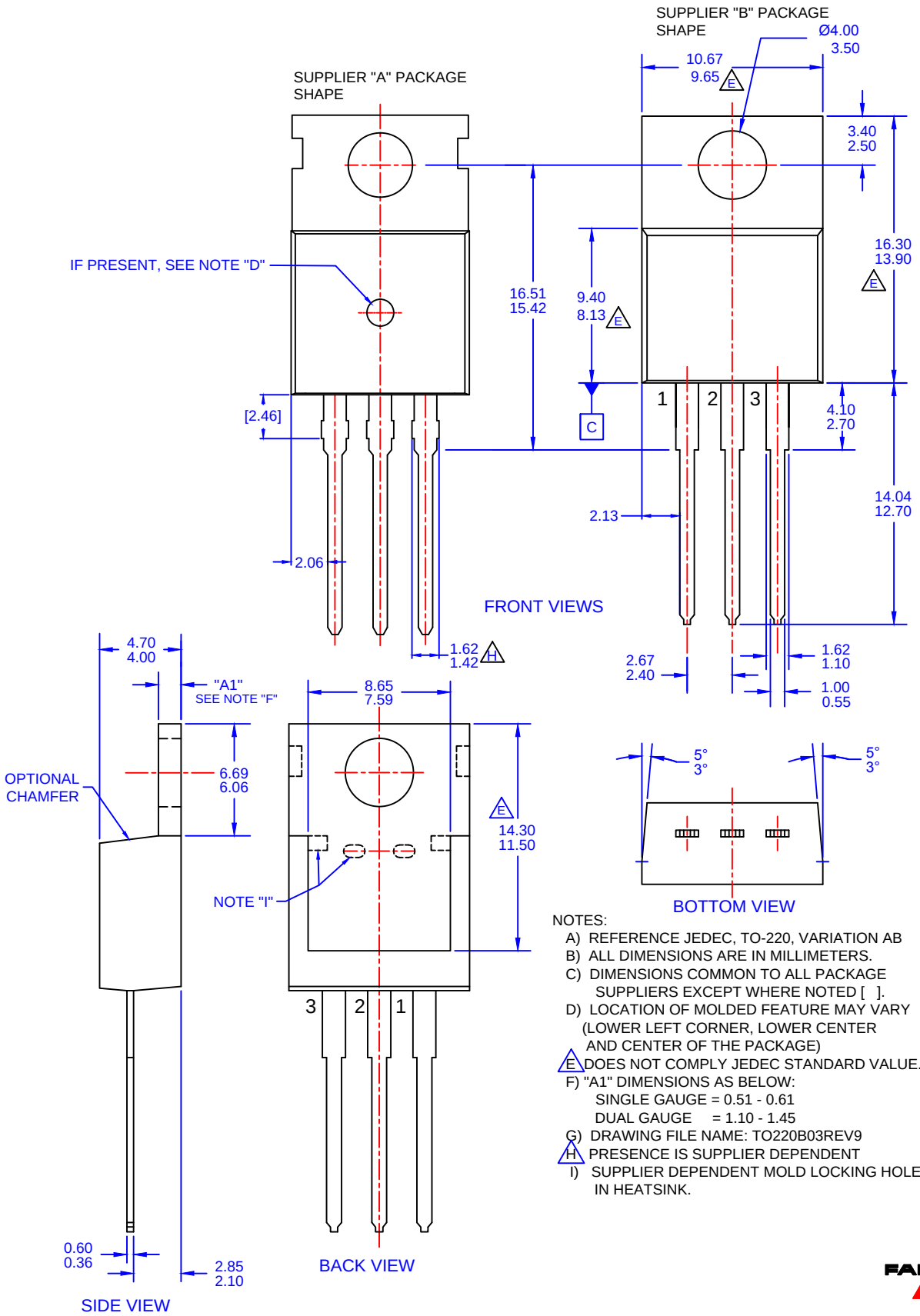


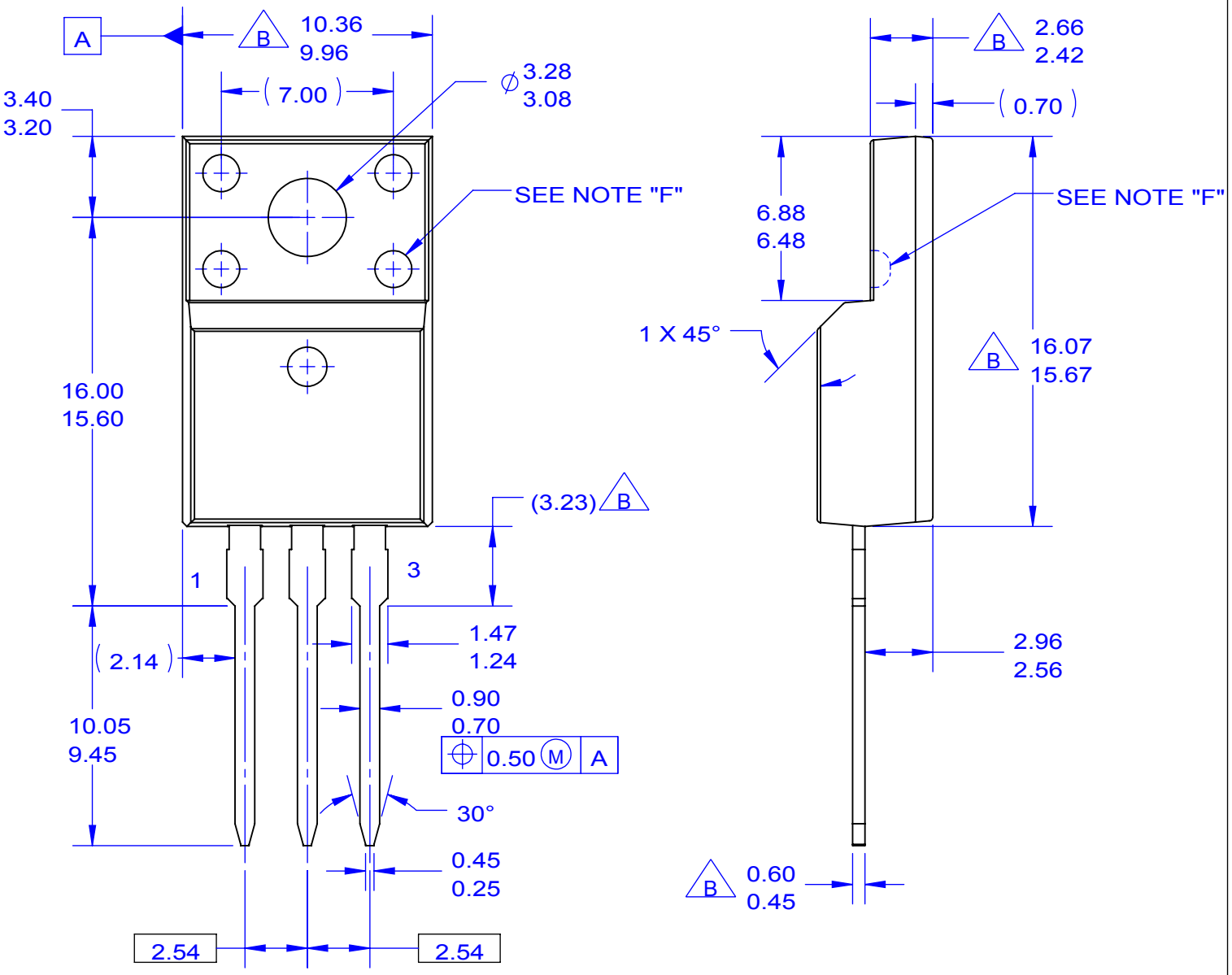
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

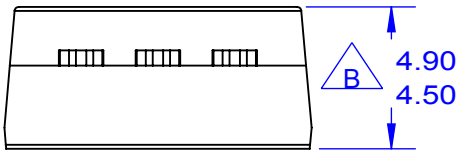




NOTES:

A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) DRAWING FILE NAME: TO220B03REV9
H PRESENCE IS SUPPLIER DEPENDENT
I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.





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NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
B DOES NOT COMPLY EIAJ STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
G. DRAWING FILE NAME: TO220M03REV5

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